64Kx32 Monolithic Pipelined Synchronous SRAM *ADVANCED**

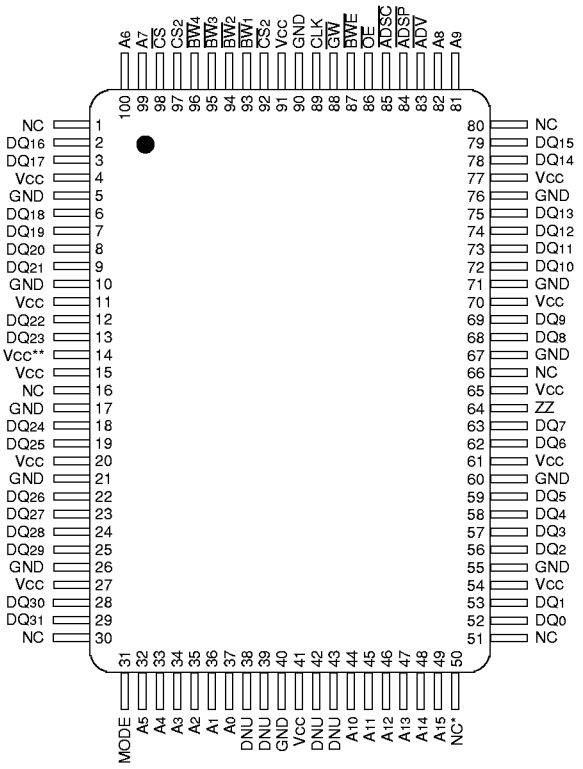
FEATURES

- Fast Access Times of 8 and 10ns
- Fast $\overline{OE}$ Access Time of 7ns
- Packaging:
  - 100-pin Ceramic Quad Flatpack, CQFP. Footprint compatible with standard 100 lead TQFP package.
- Single +3.3V ± 5 % Power Supply
- 5V-Tolerant Common Data I/O
- Individual Byte Write Control and Global Write
- Single-Cycle Disable
- Industrial and Military Temperature Ranges
- Write Pass-through Capability
- Clock Controlled, Registered, Address, Data and Control for Fully Pipelined Applications
- Internally Self-timed Write Cycle
- Burst Control Pin (Interleaved or Linear Burst)
- Snooze Mode for Reduced Power Standby
- High 30pF Output Drive Capability at Rated Access Time

** This data sheet describes a product that may or may not be under development and is subject to change or cancellation without notice.*

FIG. 1 PIN CONFIGURATION FOR WMYP64K32V-XTQX

TOP VIEW



* Pin 50 is reserved for A_{16}.

** Pin 14 does not have to be directly connected to Vcc as long as the input voltage is ≥ V_{IH}.

PIN DESCRIPTION

DQ_{0-31}	Data Inputs/Outputs
A_{0-15}	Address Inputs
$\overline{BW}_{1-4}$	Byte Writes
CLK	Clock
$\overline{CS}$, $\overline{CS}_2$ CS_2	Synchronous Chip Selects
$\overline{OE}$	Output Enable
$\overline{ADV}$	Synchronous Address Advance
$\overline{ADSP}$	Synchronous Address Status Processor
$\overline{ADSC}$	Synchronous Address Status Controller
ZZ	Snooze Enable
$\overline{BWE}$	Byte Write Enable
$\overline{GW}$	Global Write
MODE	Burst Sequence Mode
Vcc	+3.3V Power Supply
GND	Ground
NC	Not Connected
DNU	Do Not Use

GENERAL DESCRIPTION

The device integrates a 64Kx32 SRAM Core with advanced synchronous peripheral circuitry and a 2-bit burst counter. All synchronous input passes through registers controlled by a positive-edge-triggered Signal Clock Input (CLK). The synchronous inputs include all Addresses, all Data Inputs, active low Chip Select ($\overline{CS}$), two additional chip selects for easy depth expansion (CS_2, $\overline{CS}_2$), Burst Control Inputs ($\overline{ADSC}$, $\overline{ADSP}$, $\overline{ADV}$), Byte Write Enables ($\overline{BW}_{1-4}$), and Global Write ($\overline{GW}$).

Asynchronous inputs include the Output Enable ($\overline{OE}$), Clock (CLK) and Snooze Enable (ZZ). There is a Burst Mode pin (MODE) that selects between interleaved and linear burst modes. The Data Out (Q), enabled by $\overline{OE}$ is also asynchronous. WRITE cycles can be from 1 to 4 bytes wide as controlled by the write control inputs.

Burst operation can be initiated with either $\overline{ADSP}$ or $\overline{ADSC}$ input pins. Subsequent burst addresses can be internally generated as controlled by the Burst Advance pin ($\overline{ADV}$).

Address and write control are registered on-chip to simplify WRITE cycles. This allows self-timed WRITE cycles. Individual byte enables allow individual bytes to be written.

$\overline{GW}$ Low causes all Bytes to be written. WRITE pass-through makes written data immediately available at the output register during the READ cycle following a WRITE, as controlled solely by $\overline{OE}$, to improve cache system response.

This device incorporates a single-cycle deselect feature during READ cycles. If the device is immediately deselected after a READ cycle, the output bus goes to a High-Z state after the rising edge of the clock. This feature can be useful in eliminating bus contention when depth expansion is used in cache applications

The device operates from a 3.3V power supply and all inputs and outputs are TTL-compatible.

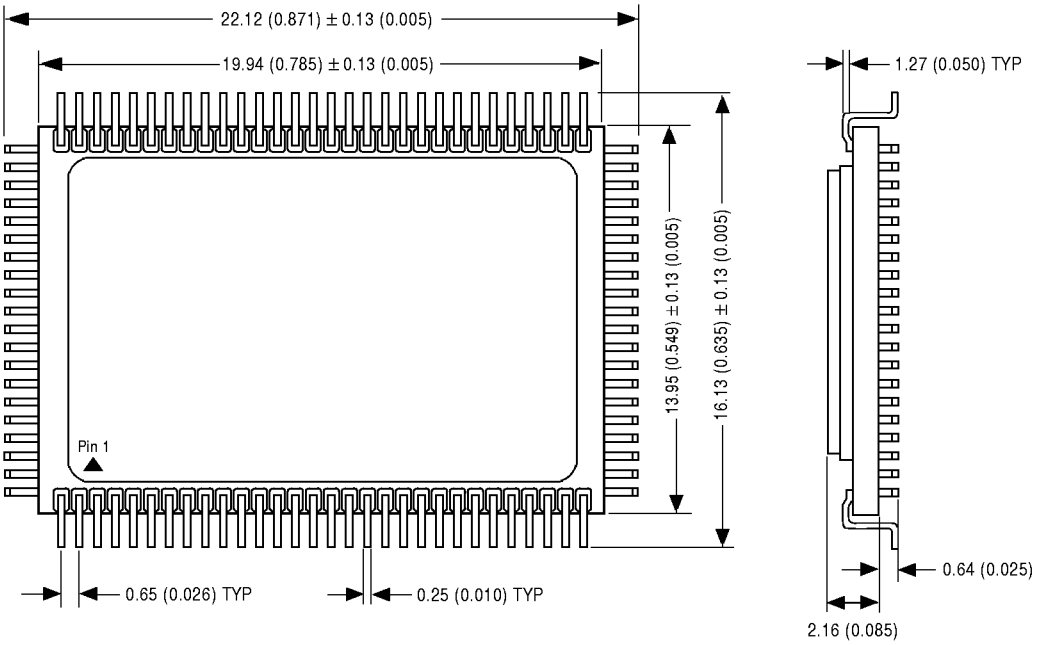
TRUTH TABLE

$\overline{CS}$	$\overline{CS}_2$	CS_2	ZZ	$\overline{ADSP}$	$\overline{ADSC}$	$\overline{ADV}$	$\overline{WRITE}$	$\overline{OE}$	CLK	DQ	Address Used	Operation
H	X	X	L	X	L	X	X	X	L→H	High-Z	N/A	Deselected Cycle, Power-down
L	X	L	L	L	X	X	X	X	L→H	High-Z	N/A	Deselected Cycle, Power-down
L	H	X	L	L	X	X	X	X	L→H	High-Z	N/A	Deselected Cycle, Power-down
L	X	L	L	H	L	X	X	X	L→H	High-Z	N/A	Deselected Cycle, Power-down
L	H	X	L	H	L	X	X	X	L→H	High-Z	N/A	Deselected Cycle, Power-down
X	X	X	H	X	X	X	X	X	X	High-Z	N/A	SNOOZE MODE, Power-down
L	L	H	L	L	X	X	X	L	L→H	Q	External Address	READ Cycle, Begin Burst
L	L	H	L	L	X	X	X	H	L→H	High-Z	External Address	READ Cycle, Begin Burst
L	L	H	L	H	L	X	L	X	L→H	D	External Address	WRITE Cycle, Begin Burst
L	L	H	L	H	L	X	H	L	L→H	Q	External Address	READ Cycle, Begin Burst
L	L	H	L	H	L	X	H	H	L→H	High-Z	External Address	READ Cycle, Begin Burst
X	X	X	L	H	H	L	H	L	L→H	Q	Next Address	READ Cycle, Continue Burst
X	X	X	L	H	H	L	H	H	L→H	High-Z	Next Address	READ Cycle, Continue Burst
H	X	X	L	X	H	L	H	L	L→H	Q	Next Address	READ Cycle, Continue Burst
H	X	X	L	X	H	L	H	H	L→H	High-Z	Next Address	READ Cycle, Continue Burst
X	X	X	L	H	H	L	L	X	L→H	D	Next Address	WRITE Cycle, Continue Burst
H	X	X	L	X	H	L	L	X	L→H	D	Next Address	WRITE Cycle, Continue Burst
X	X	X	L	H	H	H	H	L	L→H	Q	Current Address	READ Cycle, Suspend Burst
X	X	X	L	H	H	H	H	H	L→H	High-Z	Current Address	READ Cycle, Suspend Burst
H	X	X	L	X	H	H	H	L	L→H	Q	Current Address	READ Cycle, Suspend Burst
H	X	X	L	X	H	H	H	H	L→H	High-Z	Current Address	READ Cycle, Suspend Burst
X	X	X	L	H	H	H	L	X	L→H	D	Current Address	WRITE Cycle, Suspend Burst
H	X	X	L	X	H	H	L	X	L→H	D	Current Address	WRITE Cycle, Suspend Burst

NOTES:

1. X means "don't care." H means logic HIGH. L means logic LOW. $\overline{WRITE}$ = L means any one or more byte write enable signals ($\overline{BW}_1$, $\overline{BW}_2$, $\overline{BW}_3$ or $\overline{BW}_4$) and $\overline{BWE}$ are LOW or $\overline{GW}$ is LOW. $\overline{WRITE}$ = H means all byte write enable signals and $\overline{GW}$ are HIGH.
2. $\overline{BW}_1$ enables WRITEs to Byte 1 (DQ_{0-7}). $\overline{BW}_2$ enables WRITEs to Byte 2 (DQ_{8-15}). $\overline{BW}_3$ enables WRITEs to Byte 3 (DQ_{16-23}). $\overline{BW}_4$ enables WRITEs to Byte 4 (DQ_{24-31}).
3. All inputs except $\overline{OE}$ and ZZ must meet setup and hold times around the rising edge (LOW to HIGH) of CLK.
4. Wait states are inserted by suspending burst.
5. For a WRITE operation following a READ operation, $\overline{OE}$ must be HIGH before the input data setup time and held HIGH throughout the input data hold time.
6. This device contains circuitry that will ensure the outputs will be in High-Z during power-up.
7. $\overline{ADSP}$ LOW always initiates an internal READ at the L→H edge CLK. A WRITE is performed by setting one or more byte write enable signals and $\overline{BWE}$ LOW or $\overline{GW}$ LOW for subsequent L→H edge of CLK.

PACKAGE DIMENSION: 100 PIN CERAMIC QUAD FLAT PACK



ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

ORDERING INFORMATION

W M YP 64K 32 V - XX TQ X X

LEAD FINISH:
Blank = Gold plated leads
A = Solder dip leads

DEVICE GRADE:
M = Military Screened -55°C to +125°C
I = Industrial -40°C to +85°C

PACKAGE TYPE:
TQ = 100 pin Ceramic Quad Flatpack, CQFP

ACCESS TIME (ns)

Voltage Supply 3.3V ± 5%

ORGANIZATION, 64Kx32

Synchronous Pipelined SRAM

MONOLITHIC

WHITE MICROELECTRONICS